

Siddharth Krishnan

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Materials Science & Engineering (MSE)
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EDUCATION

Indian Institute of Technology Gandhinagar (IIT Gandhinagar)
B. Tech in EE [[Minors in Physics](#)]

Jul '16 – Jul '20
CPI – 9.19/10.00

PRESENTATIONS

Asymmetric Current-Voltage Characteristics in Graphene-hBN Dot-Ring Nanostructures -a numerical study
Siddharth Krishnan, Ravi Hegde
Presented at *IEEE Nano Materials and Devices Conference (NMDC)*, October 2020.

RESEARCH EXPERIENCES

IIT Gandhinagar, India
Bridge-Sabarmati Fellow in MSE
Advisor: [Prof. Raghavan Ranganathan](#)

Aug '20 – Present

Purdue University, West Lafayette
Summer Undergraduate Research Fellow at the Network for Computational Nanotechnology
Advisor: [Dr. Tillmann Kubis](#)

May – Jul '19

Indian Institute of Technology Madras (IITM)
Summer Research Intern
Advisors: [Prof. Anjan Chakravorty](#)

May – Jul '18

SUPERVISED RESEARCH PROJECTS

Development of a High-Fidelity Interatomic Potential for High Entropy Alloy Design
Advisor: [Prof. Raghavan Ranganathan](#), IITGN

Aug'20 – Present

We aim to develop an interatomic potential which can be applied to molecular dynamics (MD) to study the properties of High Entropy Alloy systems accurately. The model is based on the Embedded Atom Method and is generated using the Force Field Fitting Algorithm. The fitting data is obtained using first-principle calculations involving ab-initio MD. The model thus generated will be verified with experimental values.

Cascaded Tunneling Field Effect Transistor(CasTFET)
Advisor: [Dr. Tillmann Kubis](#), Network for Computational Nanotechnology, Purdue University

May – Jul '19

We performed calculations for Si-Ge heterostructures using a Tight-Binding Hamiltonian based Non-Equilibrium Green's Formalism to study its electronic and transport properties. We optimised the geometry of the device to improve the carrier distribution in the device for a high ON current. We also used the NEGF formalism to study various other prospective material systems for CasTFET, such as InAs-GaSb nanostructures. The calculations were performed on Purdue's HPC clusters.

Electron Transport in Graphene Nanostructures

Advisor: Prof. Ravi Hegde, IIT Gandhinagar

Aug – Dec '19

[Presented at IEEE NMDC, 2019]

We studied the peculiar I-V curves and conductance of various Graphene nanostructures, in particular Graphene-hBN heterostructure Ring Dot structure. Tight-binding model was used to study the quantum transport in these structures and highlight their interesting properties. The geometry of the structures were optimized to maximize the current asymmetry in the structures. The physics behind the asymmetry and the effect of gate voltages on the structure was also studied.

Modeling Thermal Capacitance in Hetero-junction Bipolar Transistors(HBT)

Advisor: Prof. Anjan Chakravorthy, IITGN

May – Jul '18

We conducted a numerical study on heat flow in various high frequency transistor geometries using Technology Computer Aided Design(TCAD) tools and circuit modeling tools. The insights derived from these studies were used to design a *compact model* for transient self heating in Si-Ge HBTs. The models accuracy was tested against TCAD simulation data with success.

Cost-Effective Integration of Bipolar Transistors in 180nm CMOS Technology

Advisor: Prof. Nihar Mohapatra, IITGN

May – Jul '19

We studied the various aspects of the fabrication process which strongly affect the performance of a BJT using Technology Computer Aided Design software. The geometry and doping of the device was optimized to obtain a gain β of 120 and an Early Voltage of 23 V for a bipolar NPN transistor.

SKILLS

Script: Python, C, C++, VerilogA, PBS, SLURM

Tools: Quantum Espresso, MATLAB, NEMO5, SILVACO(TCAD), Sentaurus (TCAD), \LaTeX

COURSES

Undergraduate Level Courses: Electronic Device, Introduction to Materials Science, Probability and Random Processes

Graduate Level Courses: Computational Physics, Quantum Mechanics I, Quantum Mechanics II, Statistical Mechanics, Physics of Transistors, Nanoscale Device Engineering, Lasers, Physics of 2D materials

TEACHING EXPERIENCE

Teaching Assistant for EE221(Fall 2019)

The position involved conducting concept clearing sessions, designing tests and evaluating answer scripts as well as designing problem sets for Electronic Devices course(EE221). It is a course on fundamental semiconductor physics for sophomore Electrical Engineering students.